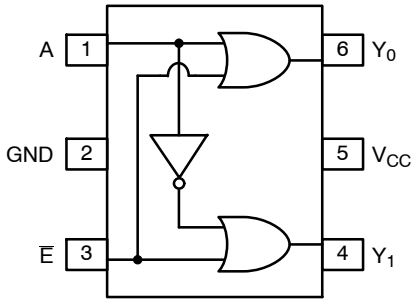
1-to-2 Decoder/ Demultiplexer

NL7SZ19

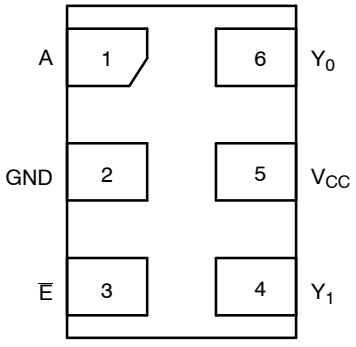
The NL7SZ19 is a 1−to−2 decoder. When the output enable ($\overline{E}$) is Low, the device passes data at input A to outputs Y0 (true) and Y1 (complement). The NL7SZ19 can also be used as a 1−to−2 demultiplexer. As a demultiplexer, data at input E is routed to either Y0 or Y1 depending on the state of A. The device operates over the voltage range from 1.65 V to 5.5 V.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.7 ns t_{PD} at V_{CC} = 5 V (Typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 32 mA at 5.0 V
- Available in SC−88, SC−74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

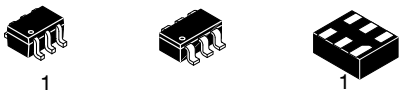


SC−88 / SC−74



UDFN6

Figure 1. Pinout (Top View)

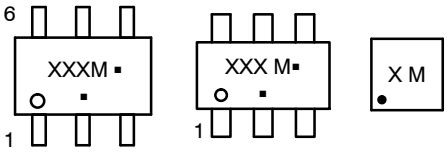


SC−88
DF SUFFIX
CASE 419B

SC−74
CASE 318F−05

UDFN6, 1.2x1.0, 0.4P
CASE 517AA−01

MARKING DIAGRAMS



X, XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

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PIN ASSIGNMENT

Pin	Function
1	A
2	GND
3	$\overline{E}$
4	Y_1
5	V_{CC}
6	Y_0

FUNCTION TABLE

$\overline{E}$	A	$Y_0 = A + \overline{E}$	$Y_1 = \overline{A} + \overline{E}$
L	L	L	H
L	H	H	L
H	H	H	H
H	L	H	H

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage	NLV	−0.5 to +7.0 −0.5 to +6.5	V
V_{IN}	DC Input Voltage	NLV	−0.5 to +7.0 −0.5 to +6.5	V
V_{OUT}	DC Output Voltage (NLV)	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +7.0 −0.5 to +7.0	V
V_{OUT}	DC Output Voltage	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +6.5 −0.5 to +6.5	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−50	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−50	mA
I_{OUT}	DC Output Source/Sink Current		±50	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SC−88 SC−74 UDFN6	377 320 154	°C/W
P_D	Power Dissipation in Still Air	SC−88 SC−74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity		Level 1	−
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	−
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
$I_{Latchup}$	Latchup Performance (Note 4)		± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri−stated.
2. Measured with minimum pad spacing on an FR4 board, using 10mm−by−1inch, 2 ounce copper trace no air flow per JESD51−7.
3. HBM tested to ANSI/ESDA/JEDEC JS−001−2017. CDM tested to EIA/JESD22−C101−F. JEDEC recommends that ESD qualification to EIA/JESD22−A115−A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		1.65	5.5	V
V_{IN}	DC Input Voltage		0	5.5	V
V_{OUT}	DC Output Voltage	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	0 0 0	V_{CC} 5.5 5.5	
T_A	Operating Temperature Range		−55	+125	°C
t_r , t_f	Input Rise and Fall Time	V_{CC} = 1.65 V to 1.95 V V_{CC} = 2.3 V to 2.7 V V_{CC} = 3.0 V to 3.6 V V_{CC} = 4.5 V to 5.5 V	0 0 0 0	20 20 10 5	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage (NLV)	−	1.65 to 1.95	0.75 x V_{CC}	−	−	0.75 x V_{CC}	−	V
			2.3 to 5.5	0.70 x V_{CC}	−	−	0.70 x V_{CC}	−	
	High−Level Input Voltage	−	1.65 to 1.95	0.65 x V_{CC}	−	−	0.65 x V_{CC}	−	V
			2.3 to 5.5	0.70 x V_{CC}	−	−	0.70 x V_{CC}	−	
V_{IL}	Low−Level Input Voltage (NLV)	−	1.65 to 1.95	−	−	0.25 x V_{CC}	−	0.25 x V_{CC}	V
			2.3 to 5.5	−	−	0.30 x V_{CC}	−	0.30 x V_{CC}	
	Low−Level Input Voltage	−	1.65 to 1.95	−	−	0.35 x V_{CC}	−	0.35 x V_{CC}	V
			2.3 to 5.5	−	−	0.30 x V_{CC}	−	0.30 x V_{CC}	
V_{OH}	High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OH} = −100 μA I_{OH} = −4 mA I_{OH} = −8 mA I_{OH} = −16 mA I_{OH} = −24 mA I_{OH} = −32 mA	 1.65 to 5.5 1.65 2.3 3 3 4.5	 V_{CC} − 0.1 1.29 1.9 2.4 2.3 3.8	 V_{CC} 1.52 2.1 2.7 2.5 4	 − − − − − −	 V_{CC} − 0.1 1.29 1.9 2.4 2.3 3.8	 − − − − − −	V
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OH} = 100 μA I_{OH} = 4 mA I_{OH} = 8 mA I_{OH} = 16 mA I_{OH} = 24 mA I_{OH} = 32 mA	 1.65 to 5.5 1.65 2.3 3 3 4.5	 − − − − − −	 − 0.08 0.12 0.24 0.26 0.31	 0.1 0.24 0.3 0.4 0.55 0.55	 − − − − − −	 0.1 0.24 0.3 0.4 0.55 0.55	V
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	1.65 to 5.5	−	−	±0.1	−	±1.0	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or V_{OUT} = 5.5 V	0	−	−	1.0	−	10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5	−	−	1.0	−	10	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

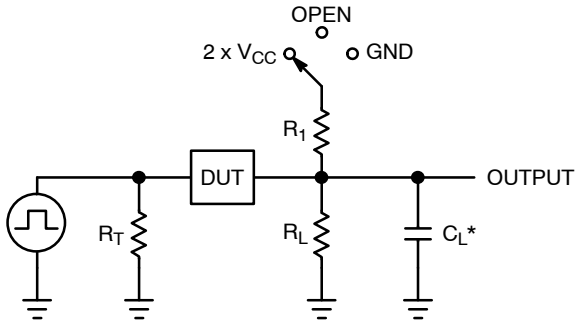
AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, A to Y (Figures 2 and 3)	R_L = 1 MΩ, C_L = 15 pF	1.65 to 1.95	–	6.2	10.5	–	11.0	ns
		R_L = 1 MΩ, C_L = 15 pF	2.3 to 2.7	–	3.6	6.0	–	6.4	
		R_L = 1 MΩ, C_L = 15 pF	3.0 to 3.6	–	2.9	4.1	–	4.5	
		R_L = 500 Ω, C_L = 50 pF		–	3.2	5.1	–	5.4	
		R_L = 1 MΩ, C_L = 15 pF	4.5 to 5.5	–	2.4	3.2	–	3.5	
		R_L = 500 Ω, C_L = 50 pF		–	2.7	4.0	–	4.3	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C_{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C_{PD}	Power Dissipation Capacitance (Note 3)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	9 11	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 Ω)
f = 1 MHz

Figure 2. Test Circuit

Test	Switch Position	C_L, pF	R_L, Ω	R_1, Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table		
t_{PLZ} / t_{PZL}	2 x V_{CC}	50	500	500
t_{PHZ} / t_{PZH}	GND	50	500	500

X = Don't Care

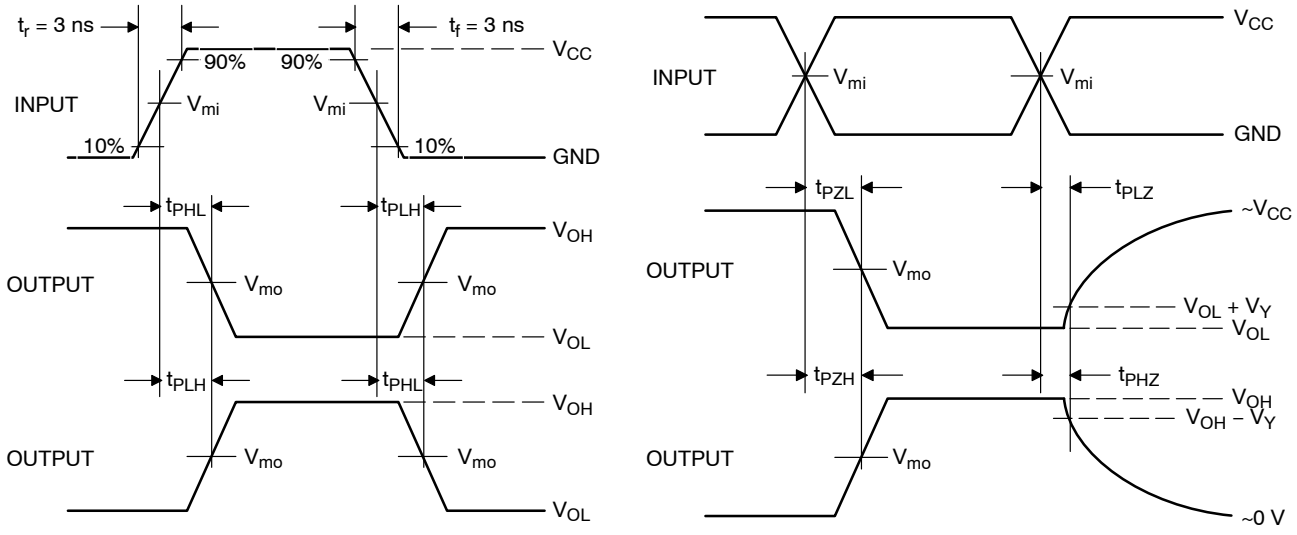


Figure 3. Switching Waveforms

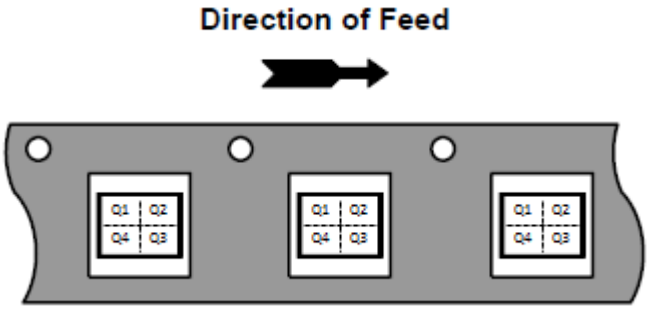
V_{CC}, V	V_{mi}, V	V_{mo}, V		V_Y, V
		t_{PLH}, t_{PHL}	t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}	
1.65 to 1.95	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.15
2.3 to 2.7	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.15
3.0 to 3.6	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.3
4.5 to 5.5	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.3

DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping†
NL7SZ19DFT2G	SC−88	LE	Q4	3000 / Tape & Reel
NLV7SZ19DFT2G*	SC−88	LE	Q4	3000 / Tape & Reel
NL7SZ19DBVT1G	SC−74	AK	Q4	3000 / Tape & Reel
NL7SZ19MUR2G**	UDFN6, 1.2 x 1.0, 0.4P	U	Q2	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.
** Please refer to NLV specifications for this device.

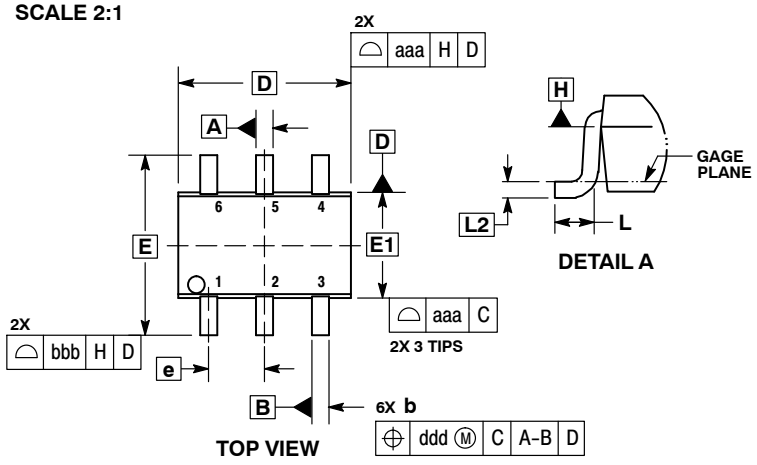
PIN 1 ORIENTATION IN TAPE AND REEL

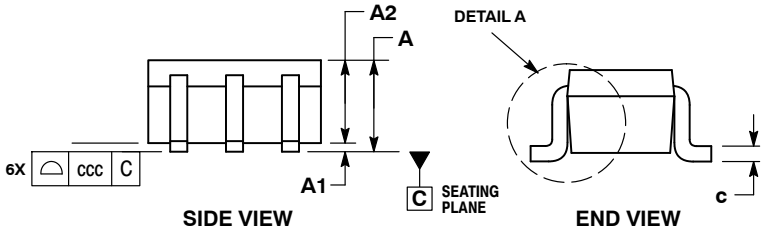


SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

1
SCALE 2:1

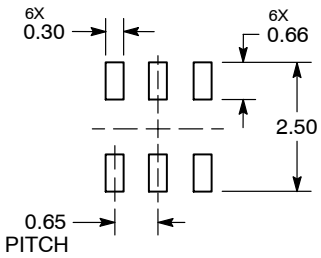




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	−−−	−−−	1.10	−−−	−−−	0.043
A1	0.00	−−−	0.10	0.000	−−−	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

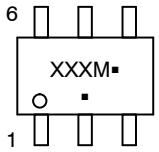
RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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DESCRIPTION:	**SC−88/SC70−6/SOT−363**	**PAGE 2 OF 2**

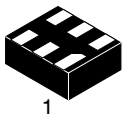
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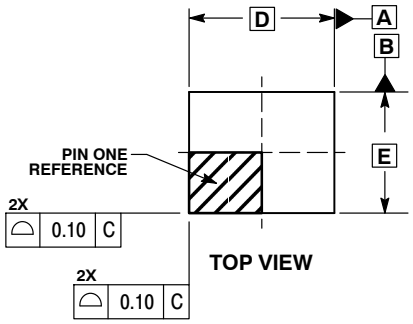
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

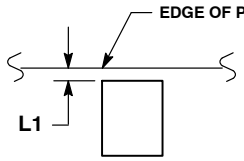
UDFN6, 1.2x1.0, 0.4P
CASE 517AA
ISSUE D

DATE 03 SEP 2010

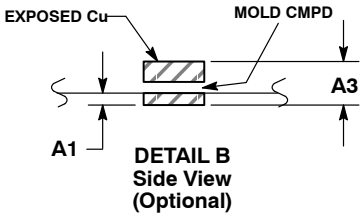


SCALE 8:1

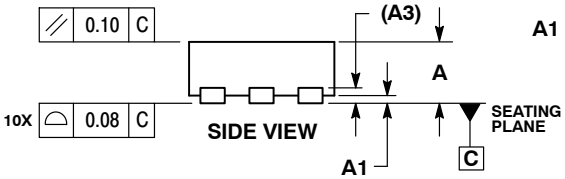


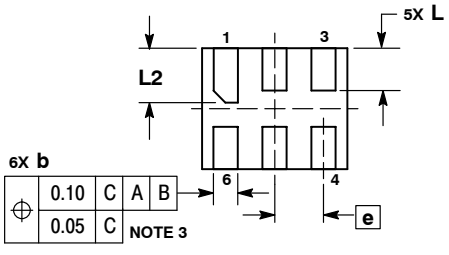


DETAIL A
Bottom View
(Optional)



DETAIL B
Side View
(Optional)





BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.127 REF	
b	0.15	0.25
D	1.20 BSC	
E	1.00 BSC	
e	0.40 BSC	
L	0.30	0.40
L1	0.00	0.15
L2	0.40	0.50

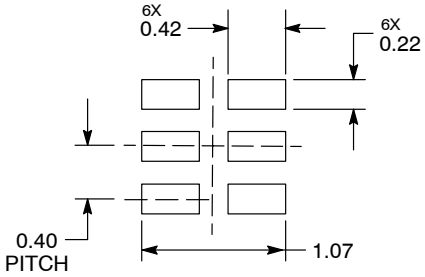
GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	6 PIN UDFN, 1.2X1.0, 0.4P	PAGE 1 OF 1

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